

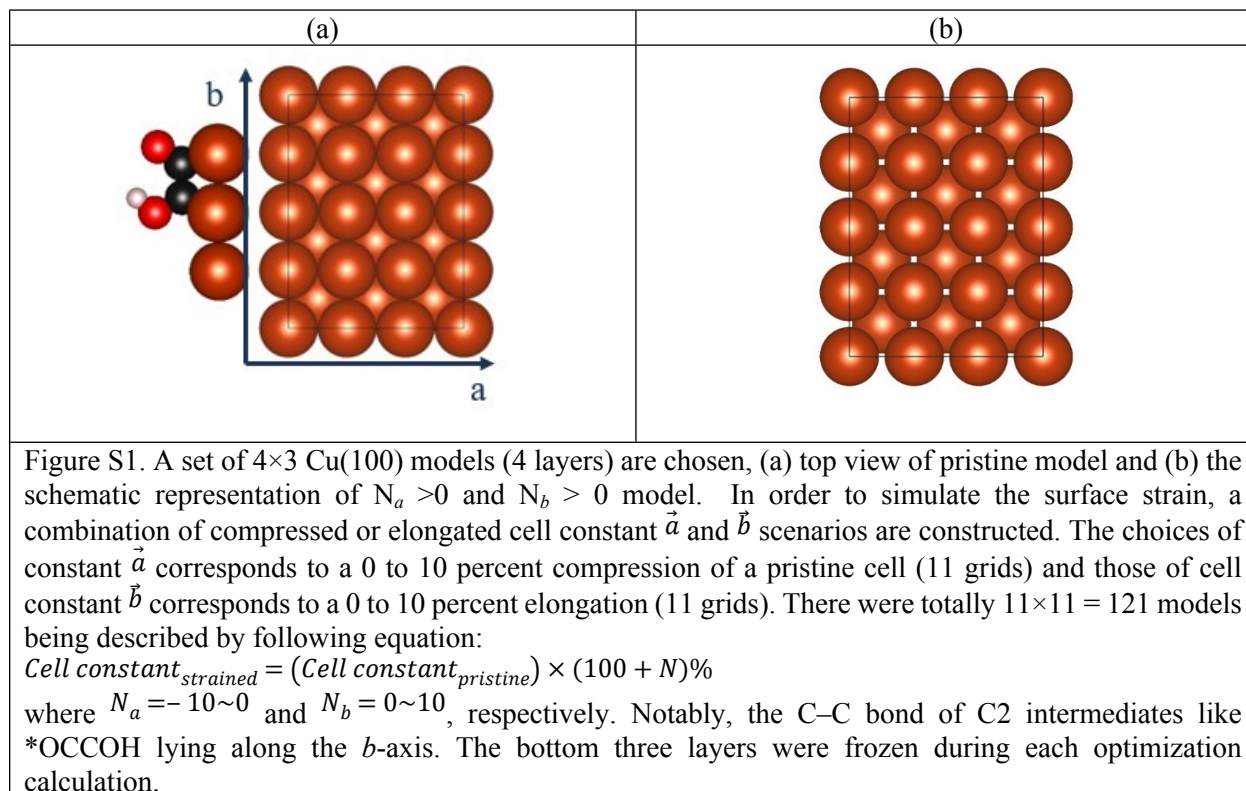
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**Enhancing C-C Bond Formation by the Surface Strain: Investigating the C2 and C3
Intermediate Formation on the Strained Cu Surfaces**

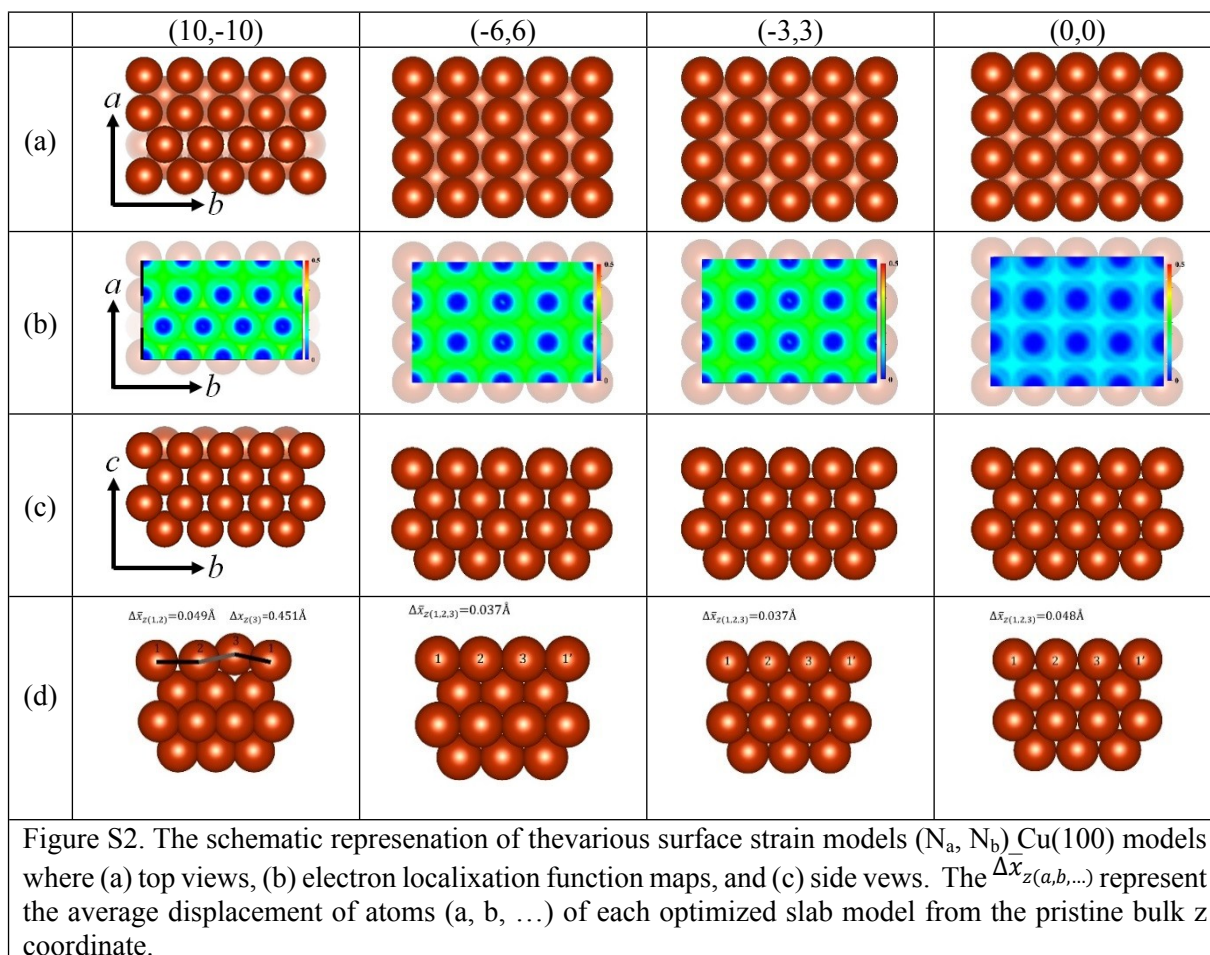
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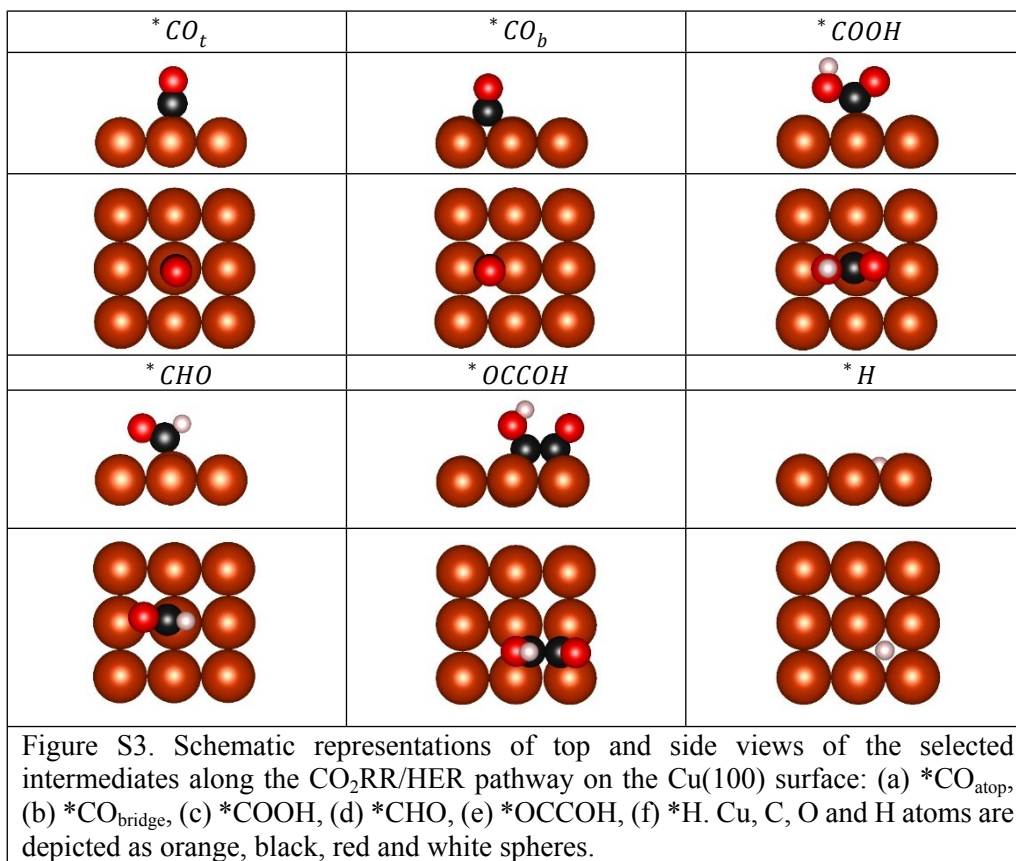
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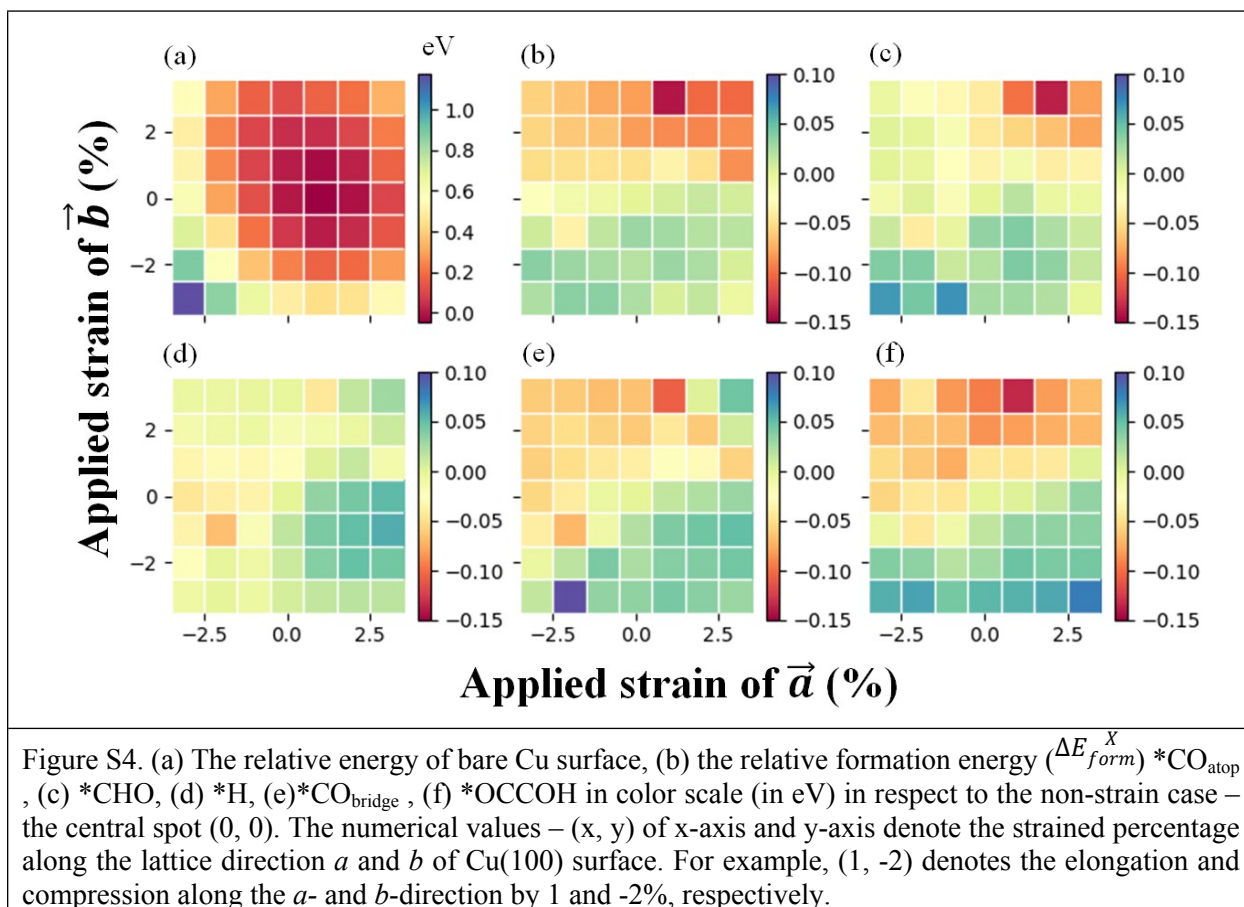
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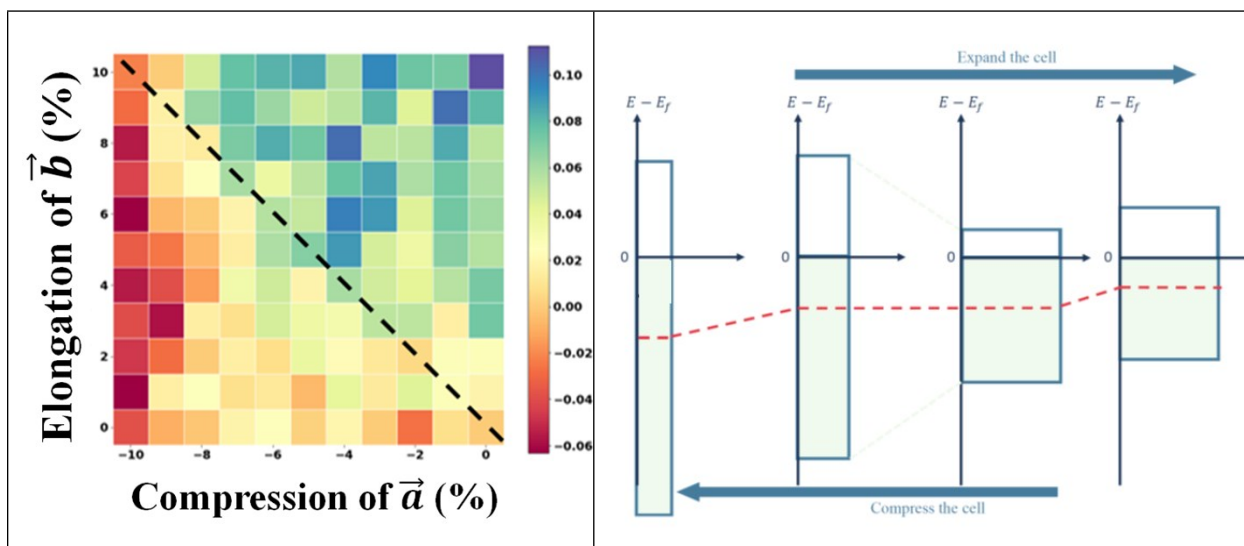
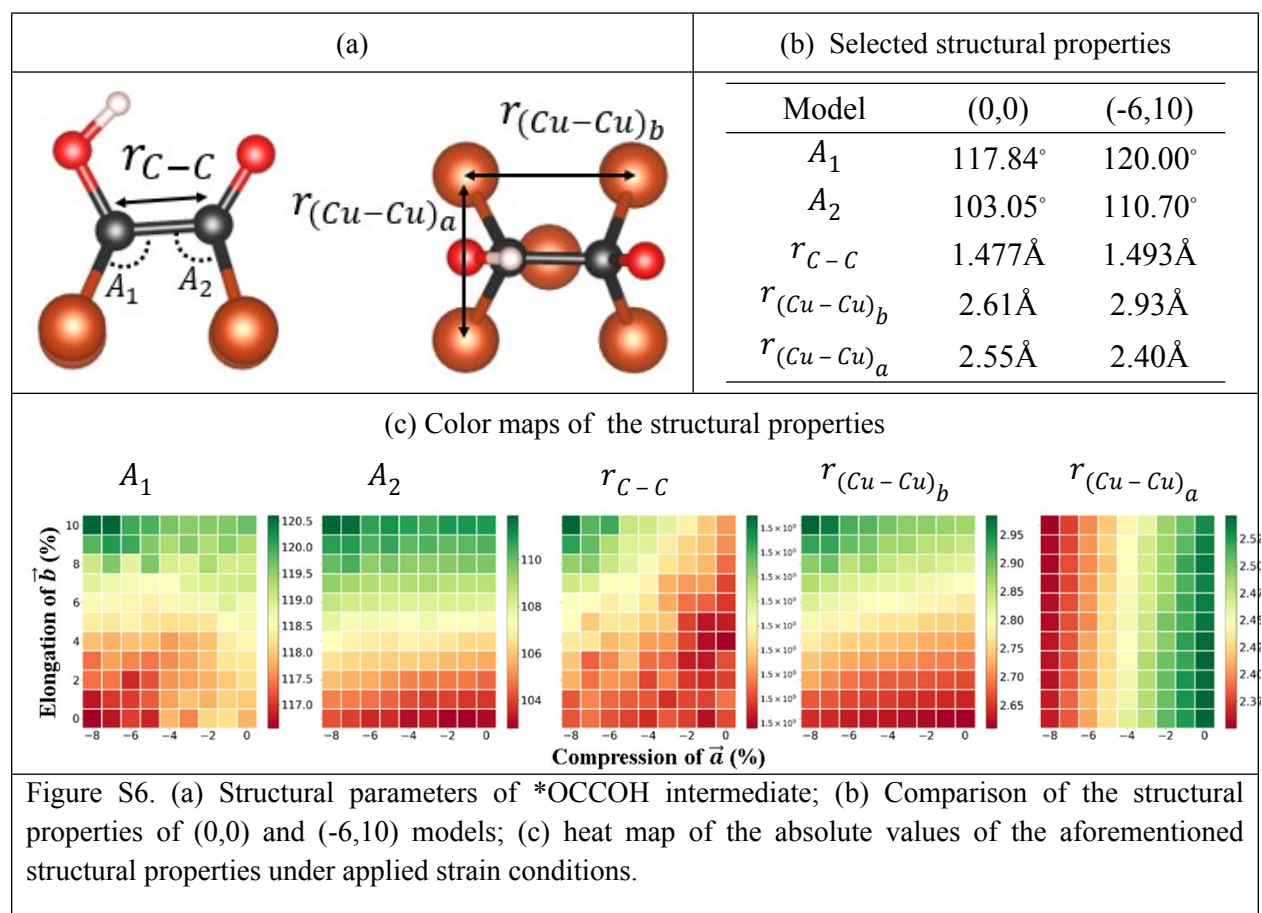
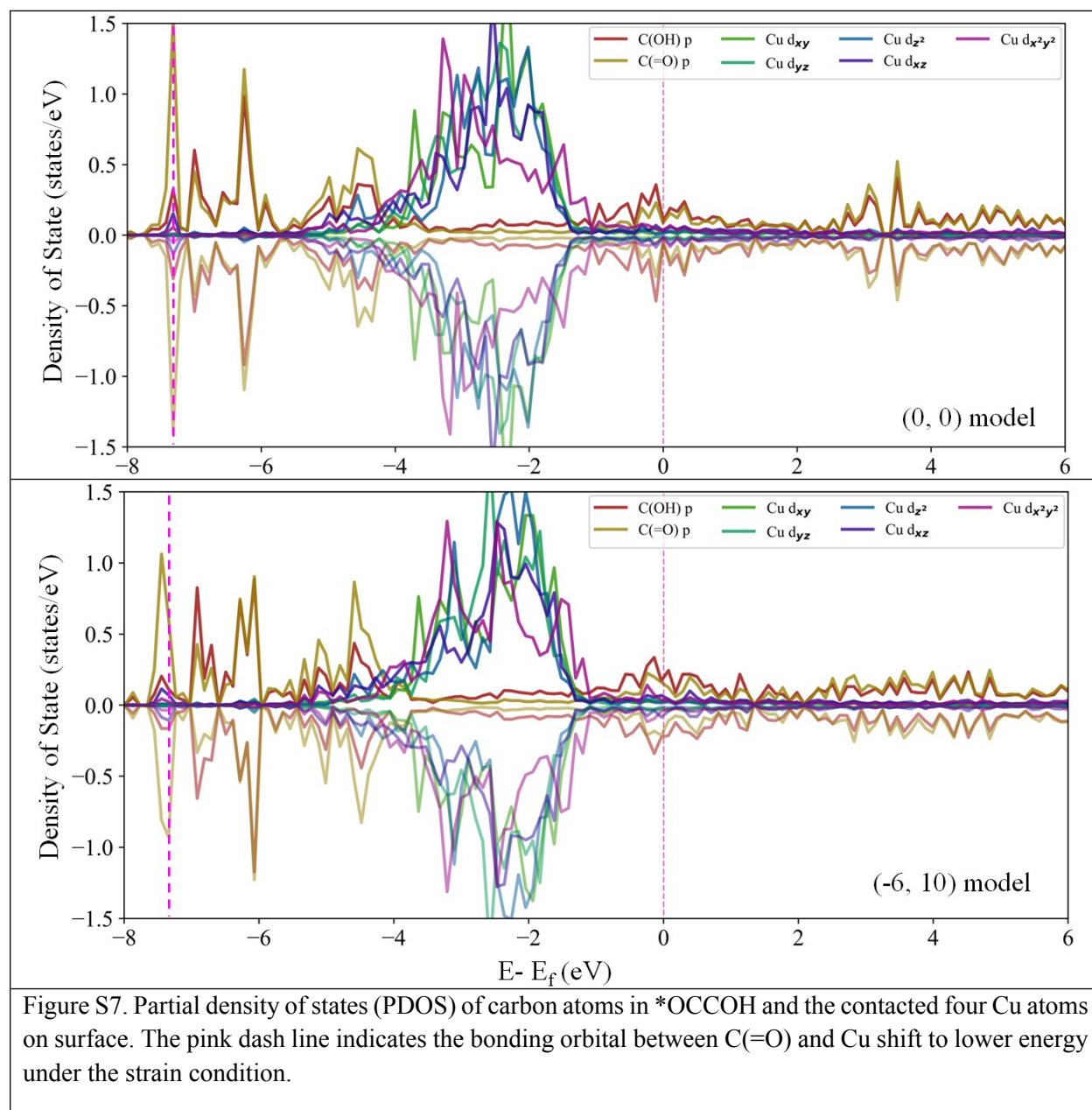


Figure S5. (a) The d-band center of the models under the applied surface strain; (b) This correlation between surface strain and d-band center elaborated by Mavrikakis et al.¹

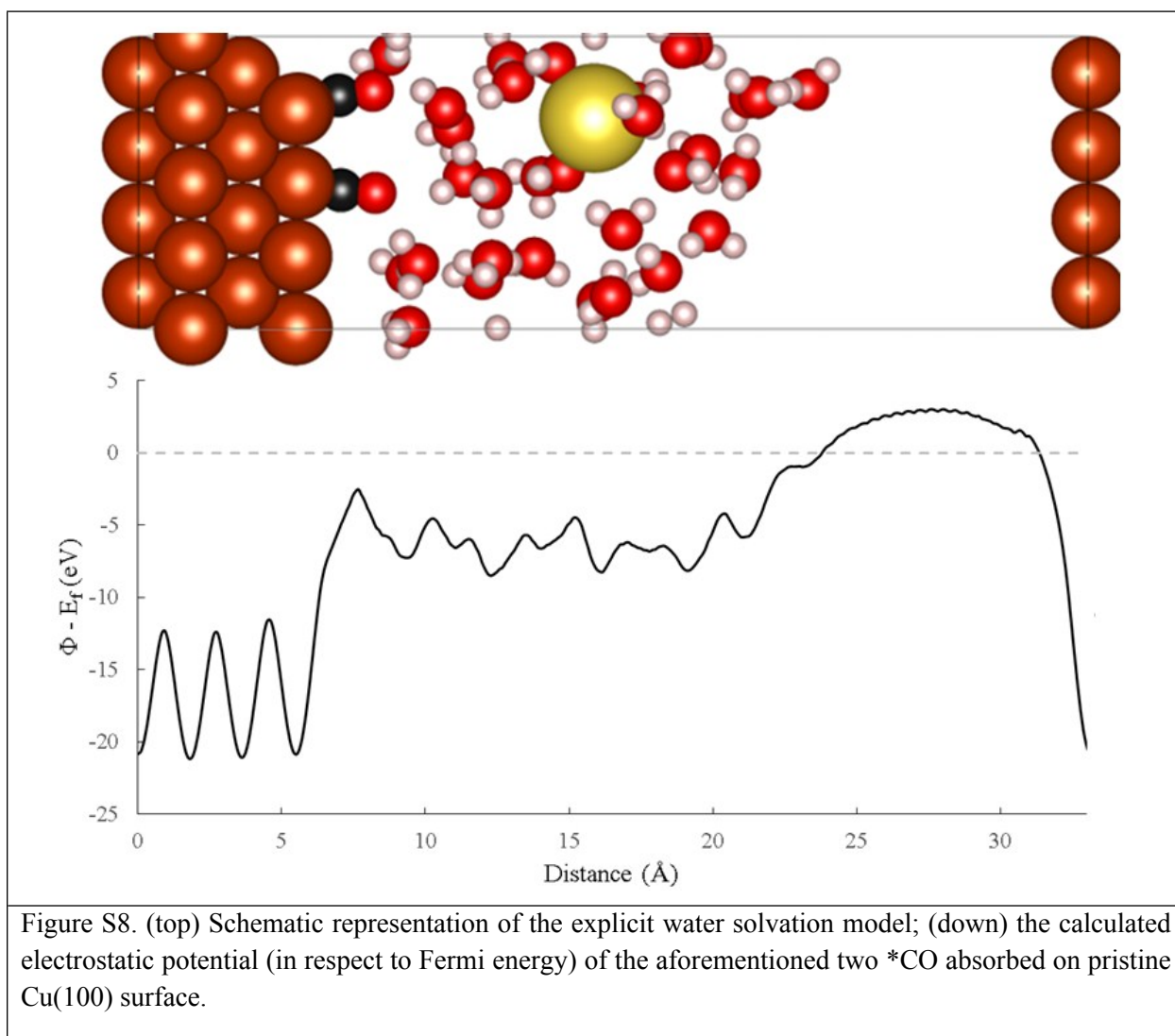
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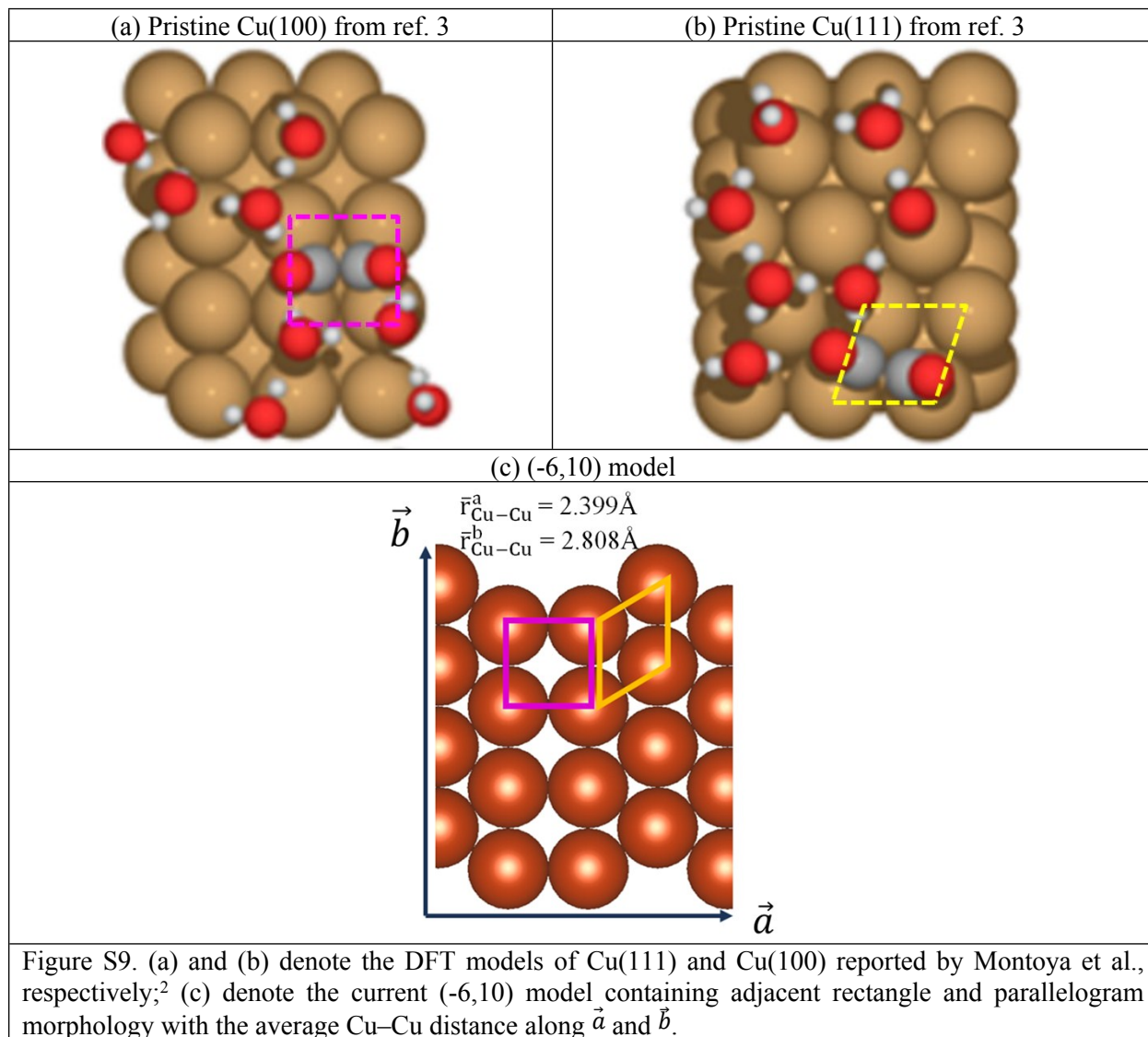
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Table S1. Correction terms calculated from frequencies for free energy calculations (in eV)

	E _{zpe}	-TS	Correction term
*OCCO_(-10,10)_ 32H ₂ O_INI	0.502	-0.269	0.233
*OCCO_(-10,10)_ 32H ₂ O_TS	0.466	-0.237	0.230
*OCCO_(-10,10)_ 32H ₂ O_FIN	0.493	-0.218	0.275
*OCCO_(-6,10)_ 32H ₂ O_INI	0.500	-0.273	0.227
*OCCO_(-6,10)_ 32H ₂ O_TS	0.464	-0.238	0.226
*OCCO_(-6,10)_ 32H ₂ O_FIN	0.499	-0.195	0.304
*OCCO_(0,0)_ 32H ₂ O_INI	0.496	-0.267	0.230
*OCCO_(0,0)_ 32H ₂ O_TS	0.461	-0.218	0.243
*OCCO_(0,0)_ 32H ₂ O_FIN	0.496	-0.202	0.294
*CCH_(-10,0)_ 32H ₂ O_INI	0.775	-0.229	0.546
*CCH_(-10,0)_ 32H ₂ O_TS	0.736	-0.305	0.431
*CCH_(-10,0)_ 32H ₂ O_FIN	0.820	-0.183	0.637
*CCH_(-10,10)_ 32H ₂ O_INI	0.770	-0.254	0.516
*CCH_(-10,10)_ 32H ₂ O_TS	0.745	-0.245	0.500
*CCH_(-10,10)_ 32H ₂ O_FIN	0.814	-0.191	0.623
*CCOH_(-10,0)_ 32H ₂ O_INI	0.930	-0.260	0.670
*CCOH_(-10,0)_ 32H ₂ O_TS	0.919	-0.286	0.633
*CCOH_(-10,0)_ 32H ₂ O_FIN	0.974	-0.273	0.702
*CCOH_(-10,10)_ 32H ₂ O_INI	0.901	-0.288	0.613
*CCOH_(-10,10)_ 32H ₂ O_TS	0.908	-0.267	0.642
*CCOH_(-10,10)_ 32H ₂ O_FIN	0.969	-0.257	0.711

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Table S2. Calculated energies of reactant (INI), TS, and product (FIN) states for the C-C coupling processes of Figure 4.

	Model	INI	TS	FIN	$\Delta E(\text{TS})$	$\Delta E(\text{rxn})$
2CO	(-10,10)_1	-666.97	-666.48	-666.71	0.49	0.26
	(-10,10)_2	-667.32	-666.83	-666.87	0.49	0.45
	(-10,10)_3	-667.41	-666.59	-666.90	0.82	0.51
	(-10,10)_4	-666.89	-666.42	-666.76	0.47	0.13
	(-10,10)_5	-667.41	-666.82	-666.93	0.59	0.48
	(-6,10)_1	-669.82	-668.96	-669.51	0.86	0.31
	(-6,10)_2	-669.99	-669.41	-669.86	0.58	0.13
	(-6,10)_3	-669.90	-669.29	-669.83	0.61	0.07
	(-6,10)_4	-670.20	-669.36	-669.84	0.84	0.36
	(-6,10)_5	-669.98	-669.43	-669.87	0.55	0.11
	(0,0)_1	-673.29	-672.73	-673.08	0.56	0.21
	(0,0)_2	-673.31	-672.60	-672.98	0.71	0.33
	(0,0)_3	-673.43	-672.87	-673.09	0.56	0.34
	(0,0)_4	-673.35	-672.78	-673.07	0.57	0.28
	(0,0)_5	-673.28	-672.84	-673.05	0.44	0.23
CCH	(-10,0)_1	-672.48	-671.94	-672.42	0.54	0.06
	(-10,0)_2	-672.66	-672.10	-672.69	0.56	-0.03
	(-10,0)_3	-672.78	-672.17	-672.74	0.61	0.04
	(-10,0)_4	-672.68	-672.07	-672.58	0.61	0.10
	(-10,0)_5	-672.67	-672.14	-672.64	0.53	0.03
	(-10,10)_1	-671.21	-670.73	-671.02	0.48	0.19
	(-10,10)_2	-671.21	-670.71	-671.15	0.50	0.06
	(-10,10)_3	-670.77	-670.24	-670.79	0.53	-0.02
	(-10,10)_4	-671.18	-670.65	-671.13	0.53	0.05
	(-10,10)_5	-671.13	-670.54	-671.03	0.59	0.10
CCOH	(-10,0)_1	-679.23	-678.61	-679.31	0.62	-0.08
	(-10,0)_2	-679.31	-678.81	-679.52	0.50	-0.21
	(-10,0)_3	-679.04	-678.40	-679.24	0.64	-0.20
	(-10,0)_4	-679.30	-678.48	-679.17	0.82	0.13
	(-10,0)_5	-679.39	-678.61	-679.22	0.78	0.17

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	(-10,10)_1	-677.54	-677.00	-677.84	0.54	-0.30
	(-10,10)_2	-678.00	-677.39	-678.24	0.61	-0.24
	(-10,10)_3	-678.09	-677.60	-678.40	0.49	-0.31
	(-10,10)_4	-678.42	-678.05	-678.66	0.37	-0.24
	(-10,10)_5	-678.48	-677.96	-678.85	0.52	-0.37
(1). The notation of model (x,y)_z denotes the strain condition (x,y) and the trial of AIMD calculations (z).						
(2). $\Delta E(\text{TS})$ and $\Delta E(\text{rxn})$ denote the reaction barrier and reaction energy, respectively.						
(3). All energy values are shown in eV.						

Table S3. The statistical details of mean relative energetics, and standard deviations.					
	Model	Term ^{1,2}	³ INI	TS	FIN
2CO	(-10,10)	E(mean)	0.00	0.57	0.37
		STD	0.25	0.15	0.16
		ZPE-T Δ S	0.23	0.23	0.28
		$\Delta G = \Delta(E+ZPE-TS)$	0.00	0.57	0.41
	(-6,10)	E(mean)	0.00	0.69	0.20
		STD	0.14	0.15	0.13
		ZPE-T Δ S	0.23	0.23	0.30
		ΔG	0.00	0.69	0.27
	(0,0)	E(mean)	0.00	0.57	0.28
		STD	0.06	0.10	0.06
		ZPE-T Δ S	0.23	0.24	0.29
		ΔG	0.00	0.58	0.34
CCH	(-10,0)	E(mean)	0.00	0.57	0.04
		STD	0.11	0.04	0.05
		ZPE-T Δ S	0.55	0.43	0.64
		ΔG	0.00	0.45	0.13
	(-10,-10)	E(mean)	0.00	0.53	0.08
		STD	0.19	0.04	0.08
		ZPE-T Δ S	0.52	0.50	0.62
		ΔG	0.00	0.51	0.18
CCOH	(-10,0)	E(mean)	0.00	0.67	-0.04

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		STD	0.13	0.13	0.18
		ZPE-TΔS	0.67	0.63	0.70
		ΔG	0.00	0.63	-0.01
	(-10,-10)	E(mean)	0.00	0.51	-0.29
		STD	0.38	0.09	0.05
		ZPE-TΔS	0.61	0.64	0.71
		ΔG	0.00	0.53	-0.19
	(1). E(mean) denotes the average energy of the five optimized solvated models.				
	$STD = \sqrt{\frac{1}{N-1} \sum_{i=1}^N (x - \bar{x})^2}$				
	(2). STD denotes the standard deviation using				
	(3). STD of INI is calculated using the sampled electronic energy of INI configurations.				

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